

Threshold features in transport through a 1D constriction.

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Suppression of electron current ΔI through a 1D channel of length L connecting two Fermi liquid reservoirs is studied taking into account the Umklapp electron-electron interaction induced by a periodic potential. This interaction causes Hubbard gaps E_H for $L \rightarrow \infty$. In the perturbative regime where $E_H \ll v_c/L$ (v_c : charge velocity), and for small deviations δn of the electron density from its commensurate values $-\Delta I/V$ can diverge with some exponent as voltage or temperature V, T decreases above $E_c = \max(v_c/L, v_c \delta n)$, while it goes to zero below E_c . This results in a nonmonotonous behavior of the conductance.

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Recent developements in the nano-fabrication technique have made the 1D interacting electron systems an experimental reality, and its quantum transport properties have been the subject of extensive studies both experimentally [1,2] and theoretically [3-15]. In realistic experimental set-ups, the quantum wire is attached to two-dimensional regions called resevoirs or leads. To describe 1D transport phenomena in this configuration a model was recently formulated of an inhomogeneous Tomonaga-Luttinger liquid (ITTL) [3,4,5]. It recovers the conductance $G = 2e^2/h$ observed experimentally even in the presence of the electron-electron interaction in the wire [1], although the previous calculations on an infinitely long wire [6,7] predicted the renormalized conductance. (see [8] for the futher development). The same puzzle holds in the Integer Quantum Hall transport, c.f. [9]. Calculation of the conductance suppressed by a weak random impurity potential in this model [10] had agreed with both the previous theoretical prediction [7] and an experiment [1] (some amendment to that result will be pointed out below). Furthermore Tarucha et al. [16] succeeded to introduce the 1D periodic potential with a periodicity of order 40nm into the wire $2\mu\text{m}$ in length and 50nm wide. This induces the Umklapp scatterings. The electron density n can be continuously controlled by the gate voltage, and one can satisfy the half-filling condition within an accessible value of n . If this condition is satisfied the system will becomes a 1D (doped) Mott insulator with the Hubbard gap E_H for the infinite length wire. Then it will offer an idealistic system to study the quantum transport in Mott and doped Mott insulators in 1D.

Inspired by these works, we study in this letter theoretically the $I - V$ characteristic of the wire of length L connected to leads taking into account the effects of the Umklapp electron-electron interactions, which can be directly compared with the experiments. We calculate the suppression of the current ΔI perturbatively in the Umklapp scatterings, and the results are summarized in Figs. 1 and 2 for a threshold structure near half filling.

There are two energy scales, i.e., the finite size energy $T_L = v_c/L$ (v_c : charge velocity) and $E_{thr} \sim v_c \delta n$ (δn : the deviation of the electron density from its value at the filling ν equal to 1/2) measuring the incommensurability. For $T, V > E_c = \max(v_c/L, E_{thr})$, the suppression of the current $-\Delta I/V$ diverges as $\max(T, V)^{4g-3}$ if the short range interaction constant g for the forward scattering is less than 3/4. For $T, V < E_c$, on the other hand, the suppression $-\Delta I/V$ goes to zero as $T, V \rightarrow 0$. Then we predict the nonmonotonous temperature and/or voltage dependence of I , which is the clear signature of the Umklapp scattering effect. For small values of g , expected when the screening length ξ_c of the interaction is much larger than the width of the channel d and $g \propto 1/\sqrt{\ln \xi_c/d}$ [11], we predict a few more threshold singularities. These features could be observed experimentally by changing the gate voltage, bias voltage, and temperature.

Our model can be derived following [4] from a 1 channel electron Hamiltonian

$$\mathcal{H} = \int dx \left\{ \sum_{\sigma} \psi_{\sigma}^{\dagger}(x) \left(-\frac{\partial_x^2}{2m^*} - E_F \right) \psi_{\sigma}(x) + \varphi(x) \rho^2(x) + [V_{imp}(x) + V_{period}(x)] \rho(x) \right\} \quad (1)$$

with the periodic potential $V_{period}(x)$ (period a) assumed to be weak enough to justify the perturbative consideration of the Umklapp backscatterings. The Fermi momentum k_F and the Fermi energy E_F is determined by the filling factor ν as $\nu = k_F a / \pi$ and $E_F \approx v_F k_F$. In Eq. (1) the function $\varphi(x) = \theta(x)\theta(L-x)$ switches on the electron-electron interaction inside the wire confined in $0 < x < L$. Contribution of the random impurity potential $V_{imp}(x)\rho(x)$ to the conductance has been considered in [7,10], some results of which we will use below. Following Haldane's generalized bosonization procedure [13] to account for the non-linear dispersion one has to write the fermionic fields as $\psi_{\sigma}(x) = \sqrt{k_F/(2\pi)} \sum \exp\{i(n+1)(k_F x + \phi_{\sigma}(x)/2) + i\theta_{\sigma}(x)/2\}$ and the electron density fluctuations as $\rho(x) = \sum \rho_{\sigma}(x)$, $\rho_{\sigma}(x) = (\partial_x \phi_{\sigma}(x))/(2\pi) \sum \exp\{in(k_F x +$

$\phi_\sigma(x)/2\}$ where summation runs over even n and $\phi_\sigma, \theta_\sigma$ are mutually conjugated bosonic fields $[\phi_\sigma(x), \theta_\sigma(y)] = i2\pi \text{sgn}(x-y)$.

After substitution of these expressions into (1) and introduction of the charge and spin bosonic fields as $\phi_{c,s} = (\phi_\uparrow \pm \phi_\downarrow)/\sqrt{2}$ the Hamiltonian takes its bose-form $\mathcal{H} = \mathcal{H}_O + \mathcal{H}_{bs}$. Here the free electron movement modified by the forward scattering interaction is described by [3,4,5]

$$\mathcal{H}_O = \int dx \sum_{b=c,s} \frac{v_b}{2} \left\{ \frac{1}{g_b(x)} \left(\frac{\partial_x \phi_b(x)}{\sqrt{4\pi}} \right)^2 \right.$$

$$\left. + g_b(x) \left(\frac{\partial_x \theta_b(x)}{\sqrt{4\pi}} \right)^2 \right\} \quad (2)$$

with $g_c(x) = g$ for $x \in [0, L]$ (g is less than 1 for the repulsive interaction and it will be assumed below), $g_c(x) = 1$, otherwise and $v_c(x) = v_F/g_c(x)$. The constants in the spin channel $g_s = 1, v_s = v_F$ are fixed by $SU(2)$ symmetry. Keeping only the most slowly decaying terms among others with the same transferred momentum one could write the backscattering interaction as

$$\mathcal{H}_{bs} = \frac{E_F^2}{v_F} \int_0^L dx \left[\sum_{\text{even } m > 0} U_m \cos(2k_{mF}mx + \frac{m\phi_c(x)}{\sqrt{2}}) + \sum_{\text{odd } m > 1} U_m \cos(\frac{\phi_s(x)}{\sqrt{2}}) \cos(2k_{mF}mx + \frac{m\phi_c(x)}{\sqrt{2}}) \right] \quad (3)$$

Difference in the transferred momentums $2k_{mF}$ is brought up by the periodical potential with the period a : $k_{mF} = k_F - \pi l/(ma) > 0$, where l is an integer chosen to minimize k_{mF} . We have omitted the first terms in both sums for they could not affect the current in the lowest perturbative order: the $m = 0$ term of the first sum can contain only the spin field and the $m = 1$ term of the second sum is assumed to transfer large momentum. The dimensionless coefficients U_m originating from $\varphi(x)$ will be assumed to be small enough to justify perturbative calculation of

the current.

Change of current due to the backscattering is given by: $\Delta I = -i/(2\sqrt{2}\pi) \int dx [\partial_x \theta_c(x), \mathcal{H}] = \sqrt{2} \int dx (\delta/\delta\phi_c(x)) \mathcal{H}_{bs}$. At finite voltage V applied symmetrically to neglect the momentum transfer variation, the average of ΔI decomposes into sum of the different backscattering mechanism contributions $\langle \Delta I_m \rangle$ in the lowest order. The even m terms involving only ϕ_c field are equal to

$$\langle \Delta I_m \rangle = -\frac{m}{4} \left(\frac{U_m E_F^2}{v_F} \right)^2 \int_{-\infty}^{\infty} dt \int \int_0^L dx_1 dx_2 < e^{im\phi_c(x_1,t)/\sqrt{2}} e^{-im\phi_c(x_2,0)/\sqrt{2}} > [e^{im(2k_{mF}(x_1-x_2)+Vt)} - h.c.]. \quad (4)$$

The current operator ΔI_m has a high energy scaling dimension $m^2g/2$ and a free electron ($g = 1$) behavior at low energy. We will see below that the integral (4) scales at low energy with $(m^2 - 1)$ exponent and with $(m^2g - 2)$ exponent at high energy. The most singular behavior is due to Umklapp backscattering at $m = 2$ with the threshold voltage $V = E_{thr} = 2k_{2F}v_c$ going to zero at the half filling. Less singular correction with $m = 4$ could become relevant at the one and three quarters fillings and so on. Expressions for the odd m terms include additionally a spin field correlator $< e^{i\phi_s(x_1,t)/\sqrt{2}} e^{-i\phi_s(x_2,0)/\sqrt{2}} >$ under

the integrals in (4). The high energy dimension of ΔI_m in this case is $m^2g/2 + 1/2$. The most singular behavior occurs to the $m = 3$ term at the one and two thirds fillings. It has two threshold energies $E_{thr,c,s} = 2k_{3F}v_{c,s}$ for $v_c \neq v_s$.

Correlator of the charge field exponents $e^{i\phi_c(x,t)}$, evolution of which is specified by $\mathcal{H}_O$, could be compiled from the correlators of the uniform TL liquid $K(x,t) = K(x,t,g,v_c)$ ($K(x,t,g,v) \equiv (\alpha\pi/\beta)^{2g}/(\prod_{\pm} \sinh^g(\pi(x/v \pm (t-i\alpha))/\beta))$) in the following way [3,10]

$$\begin{aligned} < e^{i\phi_c(x,t)} e^{-i\phi_c(y,0)} > = K(x-y,t) \prod_{\pm,n=1}^{\infty} \left(\frac{K(2nL,0)}{K(2nL \pm |x-y|,t)} \right)^{-r^{2n}} \\ & \times \prod_{n=0}^{\infty} \left(\frac{K(2(nL+x),0)K(2(nL+y),0)}{K^2(2nL+x+y,t)} \right)^{-r^{2n+1}/2} \prod_{n=1}^{\infty} \left(\frac{K(2(nL-x),0)K(2(nL-y),0)}{K^2(2nL-x-y,t)} \right)^{-r^{2n-1}/2}, \end{aligned} \quad (5)$$

Here β is inverse temperature $1/T$ and $\alpha = 1/E_F$ is the ultraviolet cut-off. This complicated form comes about through a multiple scattering at the points of joint

$x = 0, L$. As a result of the scattering the correlator $< \phi_c(x,t)\phi_c(y,0) >$ becomes an infinite sum of the uniform correlators taken along the different paths connect-

ing points x and y and undergoing reflections from the boundaries at $x = 0, L$. Each reflection brings additional factor $r = (1 - g)/(1 + g)$. The similar correlator $\langle e^{i\phi_s(x,t)} e^{-i\phi_s(y,0)} \rangle$ for spin field is $K(x - y, t, 1, v_s)$. Below we analyze the current corrections (4) for high ($T > 1/t_L = T_L$) and low ($T \ll T_L$) temperatures, respectively.

1. *High temperatures* $T > T_L$ - The uniform correlator $K(x, t)$ goes down exponentially if distance between the

points $|x|$ exceeds the inverse temperature. Therefore only paths with length less than β contribute to the correlator (5). This means that the high temperature form of the correlator (5) reduces to the first multiplier $K(x - y, t)$ up to a factor $(1 + O(\exp(-t_L/\beta)))$. Neglecting $O(T_L/T)$ quantity we can extend integration over $x_1 - x_2$ in (4) from $-\infty$ to $+\infty$. Then calculation of the $m = 2$ contribution reduces to finding Fourier transformation $F_{2g}(q, \varepsilon)$ of the correlator $K^2(x, t, g, v_c)$:

$$\langle \Delta_2 \rangle = \frac{1}{4} \left(\frac{U_2 E_F^2}{g} \right)^2 t_L \sum_{\pm} \mp F_{2g}(2E_{thr}, \pm 2V) = -2 \left(\frac{2^{2(g-1)} U_2}{\Gamma(2g)g} \right)^2 \frac{E_F^2}{T_L} \left(\frac{\pi T}{E_F} \right)^{4g-2} \sinh\left(\frac{V}{T}\right) \prod_{\pm, \pm} \Gamma(g \pm i \frac{V \pm E_{thr}}{2\pi T}) \quad (6)$$

One can easily see its behavior making use of the following asymptotics:

$$\begin{aligned} \langle \Delta_2 \rangle &\propto - \left(\frac{U_2}{g} \right)^2 \frac{E_F^2}{T_L} \left\{ \begin{aligned} &((V^2 - E_{thr}^2)/E_F^2)^{2g-1}, & V \gg E_{thr}, T \\ &((V + E_{thr})T/E_F^2)^{2g-1}, & V \approx E_{thr} \gg T \end{aligned} \right. \quad (7) \\ \langle \Delta_2 \rangle &\propto - \left(\frac{U_2}{g} \right)^2 \frac{E_F^2}{T_L} \sinh \frac{V}{T} \left\{ \begin{aligned} &e^{-E_{thr}/T} ((E_{thr}^2 - V^2)/E_F^2)^{2g-1}, & E_{thr} \gg V, T \\ &(T/E_F)^{4g-2}, & V, E_{thr} \ll T \end{aligned} \right. \end{aligned}$$

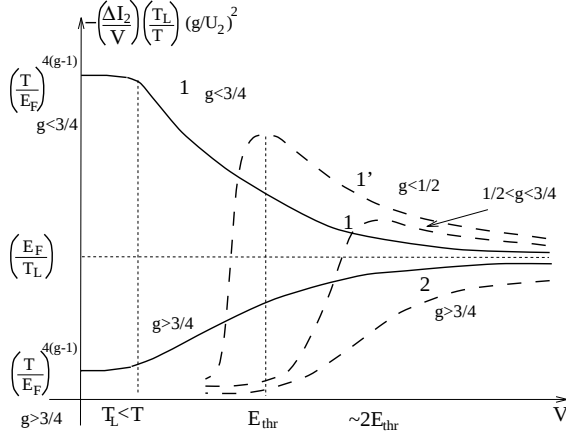


FIG. 1. Schematic voltage dependence of the high temperature current corrections produced by the $m = 2$ Umklapp interaction ΔI_2 . Solid lines, $E_{thr} = 0$; dashed lines, $E_{thr} \gg T$.

These asymptotics show that the threshold singularity in the current voltage dependence diverges as $((V - E_{thr})/T)^{2g-1}$ if $g < 1/2$ (Fig.1). It becomes stronger in the differential conductance dependence. At $g > 1/2$ the differential conductance correction dG_2 behaves as $-(V/E_F)^{4g-3}$, and saturates at $-(T/E_F)^{4g-3}$ below T , if $E_{thr} < T$; otherwise, the correction shows divergence $-((V - E_{thr})/T)^{2g-2}$ smeared over T scale near the threshold and becomes suppressed exponentially as $-\exp(-E_{thr}/T)$ below it. Generalization to the other even m current corrections needs just changing: $4g \rightarrow m^2 g$, $4k_{2F} \pm 2V \rightarrow m(2k_{mF} \pm V)$. The edge singularity is characterized by a half of the scaling dimension for ΔI_m since only one chiral component of the field ϕ_c contributes. As to the odd m terms, the two threshold energies $E_{thr c, s} = 2k_{mF} v_{c, s}$ become distinguishable if their difference exceeds T . The leading high-temperature current correction reads as:

$$\langle \Delta I_m \rangle = \frac{m}{4} \left(\frac{U_m E_F^2}{2\pi g} \right)^2 t_L v_s \sum_{\pm} \mp \int \int dq d\varepsilon F_{\frac{1}{2}}(mE_{thr s} - qv_s, \pm mV - \varepsilon) F_{\frac{m^2 g}{2}}(qv_c, \varepsilon) \quad (8)$$

Substituting zero temperature form of F_a function $F_a(q, w) = 8[\sin(\pi a)\Gamma(1 - a)]^2(\alpha/2)^{2a} \prod_{\pm}(w \pm q)^{a-1} \theta(w \pm q)$ in (8) one can gather that the current correction behaves as $-(V/E_F)^{m^2 g-1}$ at large voltage $V > E_{thr c, s}$, has a leading singularity $-((V - E_{thr c})/T)^{m^2 g/2}$ smeared over T scale near the first threshold and $-((V - E_{thr s})/T)^{m^2 g-1/2}$ near the second threshold (we assume $v_c > v_s$). Below the lowest threshold it becomes exponentially suppressed. These singularities result in the divergences of the differential conductance or higher deriva-

tives of the current in voltage. The threshold behavior of the $m = 3$ term of the differential conductance correction is divergent at $E_{thr c}$ if $g < 2/9$ and at $E_{thr s}$ if $g < 1/6$.

2. *Low temperatures* $T, V \ll T_L$ - With lowering temperature we should expect that above current correction dependences will be modulated by a πT_L quasiperiodical interference structure [14,15] and also a new low energy scaling behavior of the current correction operators will appear at $V, T < T_L$. The dominant contribution to the integral of (4) comes from long times $t \gg t_L$. One can

neglect the spaciuous dependence compared with large t in (5) and keep the multipliers with the number of reflec-

tions $n < n^* = \beta/(2t_L\pi)$ only to come to the long time asymptotics:

$$\langle e^{i\phi_c(x,t)} e^{-i\phi_c(y,0)} \rangle = e^{\gamma(T_L/T)} \left(\frac{\alpha}{t_L} \right)^{2g} \left(\frac{(\pi t_L/\beta)^2}{\sinh(\pi(t-i\alpha)/\beta) \sinh(\pi(-t+i\alpha)/\beta)} \right)^{1-z} \left(\frac{\sqrt{xy(L-x)(L-y)}}{L^2} \right)^{2rg} \quad (9)$$

where $z(T_L/T) = r^{\beta/(t_L\pi)}$ and $\gamma(T_L/T)$ approach the constant $\gamma(\infty)$ on the order of 1 as $\ln(T_L/T)z(T_L/T)$. Our asymptotic analysis following in essential Maslov's paper [10] shows that the low energy exponents approach their free electron values as $\exp[T_L \ln r/(T\pi)]$. The effect accounts for prolongation of the paths due to the finite reflection. In particular, it determines the coefficient $c(g)$

of the T^2 corrections to the non-universal zero temperature value of the conductance variation due to impurities: $\Delta G_{imp} \propto -(L/l)(T/E_F)^{g-1}(1-c(g)(T/T_L)^2)$ in a universal way [17]. After substitution of (9) into Eq. (4), the current suppression produced by the even m terms of the interaction becomes equal to:

$$\langle \Delta I_m \rangle = - \frac{m2^{m^2(1-z)} e^{m^2\gamma/2}}{\Gamma(m^2(1-z))} \left(\frac{U_m}{g} \right)^2 R_{\frac{m^2}{2}}(2mk_{mF}L) T_L \left(\frac{\pi T}{T_L} \right)^{m^2-1} \left(\frac{T_L}{E_F} \right)^{m^2(g-1)} f_{\frac{m^2}{2}}(V/T) \quad (10)$$

where function $f_a(x) = \sinh(x) \prod_{\pm} \Gamma(a \pm ix/\pi)$ characterizes the $V - T$ cross over. It approaches $\Gamma^2(a)x(1 - (\ln \Gamma(a))^n(x/\pi)^2)$ at $x \ll 1$ and $\pi(x/\pi)^{2a-1}$ at $x \gg 1$. Function R specifies the $k_F - 1/L$ cross over as:

$$R_{2g}(x) = \frac{\pi \Gamma^2(1+2rg)}{x^{1+4rg}} J_{1/2+2rg}^2(x/2) \simeq \Gamma^2(1+2rg) \begin{cases} \pi/(4^{1+4rg}\Gamma^2(3/2+2rg)), & x \ll 1 \\ 4\sin^2(x/2 - \pi rg)x^{-2-4rg}, & x \gg 1 \end{cases} \quad (11)$$

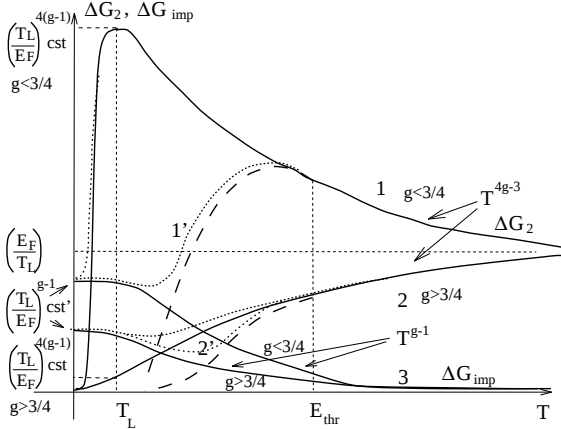


FIG. 2. Schematic temperature dependence of the conductance corrections produced by the $m = 2$ Umklapp interaction ΔG_2 at $g < 3/4$ (lines 1) and at $g > 3/4$ (lines 2) and by the random impurity potential ΔG_{imp} [7,10] (lines 3). Solid lines, $E_{thr} = 0$; dashed lines, $E_{thr} \gg T_L$. The dot lines 1 and 2 (1' and 2') are the full conductance correction at $E_{thr} = 0$ (finite E_{thr}).

The odd m corrections will meet Eq.(10) after substitution $m^2 + 1$ instead of m^2 . Combining above results we can outline a temperature dependence of the conductance correction produced by the $m = 2$ Umklapp interaction (Fig.2). Its magnitude increases/decreases following $(E_F/T_L)(T/E_F)^{4g-3}$ as T going down above T_L and follows $(T/T_L)^2(T_L/E_F)^{4g-4}$, if $E_{thr} < T_L$; otherwise, the correction starts to decrease exponentially $\exp(-E_{thr}/T)$ below E_{thr} and keeps on decreasing like

$(T/T_L)^2(T_L/E_F)^{4g-4}(T_L/E_{thr})^{2+4rg} \sin^2(2k_{2F}L - \pi rg)$ below T_L . The $T(> T_L)$ dependence is similar to that of the *conductivity* of infinite wire found by Giamarchi [12]. Similar dependence with T replaced by V could be predicted for the zero temperature differential conductance $dG_2(V)$ at $V < T_L$.

In summary under perturbative condition we have described a hierarchy of the threshold features produced by the Umklapp backscatterings at the rational values of the occupation number inside the 1D channel connecting two Fermi liquid reservoirs. In the differential conductance (its derivative) vs. voltage, the threshold structure is an asymmetric peak of width $\max(T, T_L)$ located at treshold, E_{thr} . In the conductance vs. temperature, we predicted a maximum below E_{thr} due to crossover from the Umklapp backscattering to the impurity suppression and an asymmetric minimum at E_{thr} if the interaction is strong enough.

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[1] S. Tarucha, T. Honda, and T. Saku, Solid State Commun. **94**, 413 (1995).

- [2] A. Yacobi *et al*, Solid State Commun. **101**, 77 (1996);
B.G.Levy, Physics Today, September, 19 (1996).
- [3] D. L. Maslov and M. Stone, Phys. Rev. B **52**, R5539 (1995).
- [4] V. V. Ponomarenko, Phys. Rev. B **52**, R8666 (1995).
- [5] I. Safi and H. J. Schulz, Phys. Rev. B **52**, R17040 (1995).
- [6] C. L. Kane and M. P. A. Fisher, Phys. Rev. Lett. **68**, 1220 (1992); Phys. Rev. B **46**, 15233 (1992); A. Furusaki and N. Nagaosa, Phys. Rev. **B47**, 4631 (1993).
- [7] M. Ogata and H. Fukuyama, Phys. Rev. Lett. **73**, 468 (1994); W.Apel and T.M.Rice, Phys. Rev. B **26**, 7063 (1982).
- [8] A. Kawabata, J. Phys. Soc. Jpn. **65**, 30 (1996).
- [9] M. Franco and L. Brey, Phys. Rev Lett. **77**, 1358 (1996).
- [10] D. L. Maslov, Phys. Rev. B **52**, R14368 (1995); A. Furusaki and N. Nagaosa, Phys. Rev. **B54**, R5239 (1996).
- [11] H.J.Schulz, Phys. Rev Lett. **71**, 1864 (1993).
- [12] T. Giamarchi, Phys. Rev B. **44**, 2905 (1991).
- [13] F.D.M.Haldane, Phys. Rev. Lett. **47**, 1840 (1981).
- [14] V. V. Ponomarenko, Phys. Rev. B **54**, 10326 (1996);
preprint cond-mat/9703085.
- [15] Y.Nazarov, A.Odintsov and D.Averin, unpublished.
- [16] S. Tarucha, private communications.
- [17] V. V. Ponomarenko and N. Nagaosa, in preparation.

